

International Conference on Simulation of Semiconductor Processes and Devices

**SISPAD
2025
Grenoble**

Conference Sept. 24-26
Satellite workshops Sept. 23



Conference venue

MINATEC Conference Center, 3 Parvis Louis Néel, 38054 Grenoble, FRANCE.

Technical areas

Important dates (planned)

Two-pages abstract*	April 8, 2025
Notification of acceptance	May 27, 2025
Extended 4-pages final paper*	June 24, 2025
Early registration	July 15, 2025
Late registration	August 19, 2025

*Submissions should be made through the website:

<https://sispad2025.inviteo.fr/>

- ✓ Modeling and simulation of all types of semiconductor devices, including FinFETs, GAA FETs, ultra-thin SOI devices, emerging memory devices, new material-based nanodevices, optoelectronic devices, TFTs, sensors, power electronic devices, spintronic devices, tunnel FETs, SETs, organic electronic devices, and bioelectronic devices;
- ✓ Modeling and simulation of all sorts of semiconductor processes, including first principles material design, and growth simulation of nano-scale fabrication;
- ✓ Fundamental aspects of device modeling and simulation, including quantum transport, thermal transport, fluctuation, noise, and reliability;
- ✓ Compact modeling for circuit simulation, including low-power, high frequency, and power electronics applications;
- ✓ Process/device/circuit co-simulation in context with system design and verification;
- ✓ Equipment, topography, lithography modeling;
- ✓ Interconnect modeling, including noise and parasitic effects;
- ✓ Numerical methods and algorithms, including grid generation, user-interface, and visualization;
- ✓ Metrology for the modeling of semiconductor devices and processes;
- ✓ Multiscale approach from First Principles to TCAD simulations;
- ✓ Artificial intelligence, Neural Network, Differentiable programming;
- ✓ Neuromorphic devices and quantum computing;
- ✓ Multi-physics simulation.

Organizing Committee

J-C. Barbé (CEA-Leti, chair), D. Rideau (STMicroelectronics, co-chair);
S. Martinie (CEA-Leti, TPC chair), B. Rae (STMicroelectronics, TPC co-chair);
P. Blaise (SILVACO, workshop chair), F. Triozon (CEA-Leti, workshop co-chair);
S. Barbier (CEA-Leti, local org.).

